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(54) **MEMORY DEVICE AND METHOD OF
MANUFACTURING THE SAME**

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(57)

ABSTRACT

Provided are a memory device and a method of manufacturing the same. The memory device includes: a stack structure; a first source/drain region and a second source/drain region located in a substrate beside the stack structure; a first self-aligned contact connected to the first source/drain region; a second self-aligned contact connected to the second source/drain region; a first liner structure located between the first self-aligned contact and a first sidewall of the stack structure; and a second liner structure located between the second self-aligned contact and a second sidewall of the stack structure. The first liner structure and the second liner structure are not connected and do not cover the stack structure.

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